KP5000-POWER THYRISTOR

6000-6500 V_{DRM}

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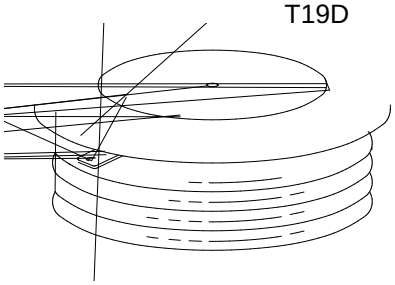
FREE FLOATING TYPE THYRISTOR FOR PHASE CONTROL APPLICATIONS

Features:

T19D



ELECTRICAL CHARACTERISTICS AND RATINGS

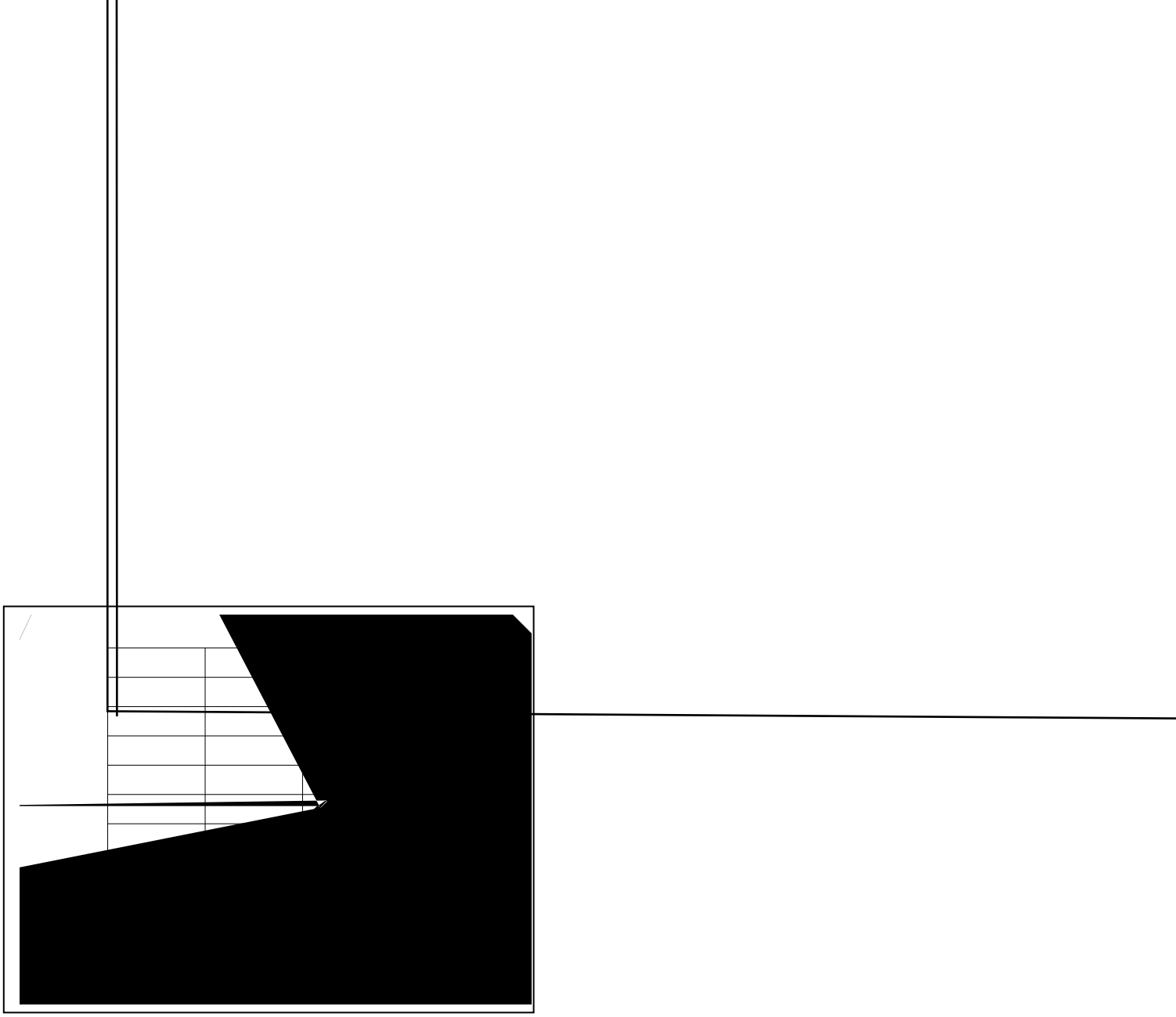
Blocking - Off State

Device Type	V_{RRM} (1)	V_{DRM} (1)	V_{RSM} (1)
KP5000/60	5100	5100	6000
KP5000/62	5300	5300	6200
KP5000/65	5600	5600	6500

V_{RRM} = Repetitive peak reverse voltage
V_{DRM} = Repetitive peak off state voltage
V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state leakage	I_{RRM}/I_{DRM}	15 mA 350 mA (3)
Critical rate of voltage rise	dv/dt (4)	2000 V/ s

Conducting - On State

Gating

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Peak gate power dissipation	P_{GM}		20		W	
Average gate power dissipation	$P_{G(AV)}$		4		W	
Gate-trigger current	I_{GT}		350		mA	V_D =12 V;R_L = 3 ohms;T_j = +25 ^oC
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